Tomasz Slupinski

List of Publications by Year
in descending order

62	773	687220 13	526166 27
papers	citations	h-index	g-index

63	63	63	664
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Optically detected magnetic resonance of indirect excitons in an ensemble of (In,Al,Ga)As/(Al,Ga)As quantum dots. Physical Review B, 2021, 104, .	1.1	3
2	Optimization of MBE Growth Conditions of In0.52Al0.48As Waveguide Layers for InGaAs/InAlAs/InP Quantum Cascade Lasers. Materials, 2019, 12, 1621.	1.3	8
3	Radiative recombination and other processes related to excess charge carriers, decisive for efficient performance of electronic devices. Lithuanian Journal of Physics, 2018, 58, .	0.1	5
4	Donor-deactivating defects above the equilibrium doping limit in GaAs:Te,Ge and GaAs:Te studied by annealing and Hall effect under pressure. Journal of Crystal Growth, 2017, 468, 433-438.	0.7	1
5	Distributed Bragg reflectors obtained by combining Se and Te compounds: Influence on the luminescence from CdTe quantum dots. Journal of Applied Physics, 2016, 119, 183105.	1.1	9
6	Efficient Emission from InAlGaAs Single Quantum Dots with Low Lattice Misfit and AlGaAs Indirect Bandgap Barrier. Acta Physica Polonica A, 2016, 130, 1229-1232.	0.2	1
7	MBE grown microcavities based on selenium and tellurium compounds. Journal of Crystal Growth, 2014, 401, 499-503.	0.7	10
8	MBE growth and characterization of a IIâ€“VI distributed Bragg reflector and microcavity lattice-matched to MgTe. Journal of Crystal Growth, 2013, 378, 266-269.	0.7	14
9	Ultra low density of CdTe quantum dots grown by MBE. Journal of Crystal Growth, 2013, 378, 274-277.	0.7	11
10	Local Structure Around Te in Heavily Doped GaAs:Te using X-Ray Absorption Fine Structure. Acta Physica Polonica A, 2012, 121, 879-882.	0.2	1
11	MBE Growth of CdTe/ZnTe Quantum Dots with Single Mn Ions. Acta Physica Polonica A, 2012, 122, 1056-1058.	0.2	5
12	MBE Growth and Characterization of a III-V Distributed Bragg Reflectors and InAs Quantum Dots. Acta Physica Polonica A, 2012, 122, 984-987.	0.2	1
13	Studies of Magnetoresistance in GaAs:Te Crystals with Structural Disorder at Doping Limit. Acta Physica Polonica A, 2011, 119, 726-728.	0.2	2
14	Free Carrier Scattering in Metallic n-GaAs in the Presence of Static Lattice Distortions Due to a Partial Chemical Order of Impurities. Acta Physica Polonica A, 2009, 116, 979-982.	0.2	4
15	Highâ€resolution Xâ€ray diffraction study of CZâ€grown GaAsP crystals. Physica Status Solidi (A) Applications and Materials Science, 2007, 204, 2578-2584.	0.8	0
16	Hole Transport in Impurity Band and Valence Bands Studied in Moderately Doped GaAs:Mn Single Crystals. Acta Physica Polonica A, 2007, 112, 325-330.	0.2	3
17	Coupled plasmonâ€“LO-phonon modes at high-magnetic fields. Physical Review B, 2006, 74, .	1.1	13
18	Magnetization Reversal Process of Submicrometer-Scale Hall Bars of Ferromagnetic Semiconductorp-In0.97Mn0.03As. Japanese Journal of Applied Physics, 2004, 43, 2097-2100.	0.8	0

#	Article	IF	Citations
19	Ferromagnetic resonance in epitaxial(In0.53Ga0.47)1â^'xMnxAs: Angle- and temperature-dependent studies. Physical Review B, 2004, 70, .	1.1	16
20	Dynamics of photoinduced magnetization rotation in ferromagnetic semiconductorp-(Ga,Mn)As. Physical Review B, 2004, 69, .	1.1	64
21	Ultrafast softening in InMnAs. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 20, 412-418.	1.3	22
22	Carrier-induced ferromagnetic order in the narrow gap IIIâ€"V magnetic alloy semiconductor (In,Mn)Sb. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 20, 333-337.	1.3	33
23	High-field cyclotron resonance studies of InMnAs-based ferromagnetic semiconductor heterostructures. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 978-982.	1.3	8
24	Title is missing!. Journal of Superconductivity and Novel Magnetism, 2003, 16, 107-110.	0.5	8
25	Alloying (In,Mn)As and (Ga,Mn)As: Ferromagnetic (In,Ga,Mn)As Lattice-Matched to InP. Journal of Superconductivity and Novel Magnetism, 2003, 16, 45-49.	0.5	2
26	Rotation of Ferromagnetically Coupled Mn Spins in (Ga,Mn)As by Hole Spins. Journal of Superconductivity and Novel Magnetism, 2003, 16, 411-414.	0.5	1
27	Ultrafast Optical Manipulation of Ferromagnetic Order in InMnAs/GaSb. Journal of Superconductivity and Novel Magnetism, 2003, 16, 373-377.	0.5	18
28	Title is missing!. Journal of Superconductivity and Novel Magnetism, 2003, 16, 439-442.	0.5	3
29	Title is missing!. Journal of Superconductivity and Novel Magnetism, 2003, 16, 449-452.	0.5	5
30	Theoretical and experimental studies of cyclotron resonance in p-type InAs and InMnAs at ultrahigh magnetic fields. Journal of Applied Physics, 2003, 93, 6897-6899.	1.1	11
31	Terahertz dynamics of photogenerated carriers in ferromagnetic InGaMnAs. Journal of Applied Physics, 2003, 93, 8286-8288.	1.1	6
32	PARALLEL TRANSPORT PROPERTIES OF p-In_{1â^'x}Mn_xAs / n-InAs JUNCTION. , 2003, , .		0
33	MAGNETIZATION REVERSAL BY OPTICAL SPIN INJECTION AND ITS MEMORIZATION EFFECT IN (Ga, Mn) As THIN FILMS. , 2003, , .		0
34	Effect of Optical Spin Injection on Ferromagnetically Coupled Mn Spins in the III-V Magnetic Alloy Semiconductor(Ga,Mn)As. Physical Review Letters, 2002, 88, 137202.	2.9	157
35	Electronic structure ofIn1â^'xMnxAsstudied by photoemission spectroscopy: Comparison withGa1â^'xMnxAs. Physical Review B, 2002, 65, .	1.1	53
36	Ferromagnetic semiconductor (In,Ga,Mn)As with Curie temperature above 100 K. Applied Physics Letters, 2002, 80, 1592-1594.	1.5	53

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37	Interlayer coupling in (In,Mn)As/InAs/(In,Mn)As magnetic semiconductor trilayer structures. Journal of Applied Physics, 2002, 91, 7902.	1.1	8
38	Photo-carrier-induced magnetism in (In,Mn)As/GaSb magnetic alloy semiconductor heterostructures. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 516-520.	1.3	9
39	Preparation of ferromagnetic (In,Mn)As with relatively low hole concentration and Curie temperature 50K. Journal of Crystal Growth, 2002, 237-239, 1326-1330.	0.7	30
40	Preparation of ferromagnetic quaternary (In,Ga,Mn)As. Journal of Crystal Growth, 2002, 237-239, 1331-1333.	0.7	2
41	Inelastic light scattering on coupled plasmon-LO phonon modes in high magnetic fields. Physica B: Condensed Matter, 2001, 298, 216-220.	1.3	4
42	Effect of light illumination on the process of magnetization reversal in carrier-induced ferromagnetic semiconductors. Physica E: Low-Dimensional Systems and Nanostructures, 2001, 10, 201-205.	1.3	6
43	Control of magnetization reversal process by light illumination in ferromagnetic semiconductor heterostructure p-(In,â€ŠMn)As/GaSb. Applied Physics Letters, 2001, 78, 518-520.	1.5	97
44	Local order of Te impurity atoms and free electron concentration in heavily doped GaAs:Te. Thin Solid Films, 2000, 367, 227-231.	0.8	5
45	X-ray diffuse scattering characterization of microdefects in highly Te-doped annealed GaAs crystals. Journal Physics D: Applied Physics, 1998, 31, 1883-1887.	1.3	6
46	Thermal expansion of GaAs:Te and AlGaAs:Te at low temperatures. Journal of Applied Physics, 1997, 82, 4678-4680.	1.1	11
47	Characterization of microdefects in GaAs crystals with high-resolution X-ray diffractometry. Nuovo Cimento Della Societa Italiana Di Fisica D - Condensed Matter, Atomic, Molecular and Chemical Physics, Biophysics, 1997, 19, 625-635.	0.4	5
48	First X-Ray Evidence of Heterogeneous Impurity Correlations in Very Highly Doped n-GaAs. Acta Physica Polonica A, 1997, 92, 971-975.	0.2	0
49	Coexistence of DX and A₁ States in Highly Doped GaAs:Ge, Te and GaAs:Si, Te. Physica Status Solidi (B): Basic Research, 1996, 198, 181-186.	0.7	2
50	DLTS Investigations of the Distorted Configuration of the EL2 Defect Stabilized under High Hydrostatic Pressure in GaAs1â^'xPx. Physica Status Solidi (B): Basic Research, 1996, 198, 193-198.	0.7	1
51	Te Shallow Donor Solubility Mechanism in GaAs. Acta Physica Polonica A, 1996, 90, 1080-1084.	0.2	3
52	On Correlations between Extended Defects Formation and Electron Concentration Changes Caused by Annealing of GaAs:Te. Acta Physica Polonica A, 1996, 90, 739-742.	0.2	0
53	Scanning Tunneling Microscopy Studies of GaAs1-xPx Single Crystals. Materials Research Society Symposia Proceedings, 1995, 378, 83.	0.1	0
54	Stabilization of the Distorted Configuration of the EL2 Defect Induced by the Free Electron Capture in GaAsP. Acta Physica Polonica A, 1995, 88, 881-884.	0.2	2

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55	Large negative persistent photoconductivity of bulk GaAs1-xPx () single crystals. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1993, 21, 325-328.	1.7	0
56	Direct proof of two-electron occupation of Ge-DXcenters in GaAs codoped with Ge and Te. Physical Review Letters, 1993, 71, 3529-3532.	2.9	27
57	Direct Evidence for Two-Electron Occupation of Ge-DX Centers in GaAs. Materials Science Forum, 1993, 143-147, 1019-1024.	0.3	3
58	Highly Compensated GaAs Crystal Obtained by Molecular CO Doping. Acta Physica Polonica A, 1993, 84, 669-672.	0.2	0
59	Deep Level Transient Spectroscopy Measurements of an Acceptor-like State of Metastable EL2 in GaAs and GaAsP. Acta Physica Polonica A, 1993, 84, 673-676.	0.2	0
60	On the Pinning of the Fermi Level by Germanium A₁^{0/+}Deep Donor State in GaAs Codoped with Ge and Te. Acta Physica Polonica A, 1993, 84, 807-811.	0.2	0
61	Hydrostatic-Pressure Deep Level Transient Spectroscopy Study of the Heteroantisite Antimony Level in GaAs. Acta Physica Polonica A, 1992, 82, 841-844.	0.2	0
62	Ultrafast optical manipulation of ferromagnetic order in InMnAs/GaSb. , 0, , .		0